Hi-Tech Institute of Engineering & Technology		
DEPARTMEN	DEPARTMENT OF APPLIED SCIENCE	
1 ST MODEL PAPER, ODD SEMESTER-2023-24,		
Semester:1st	Course/Branch:B.Tech	
Subject Code:BEC 101	Subject Name: FUNDAMENTALS OF	
	ELECTRONICS ENGINEERING	
Faculty Name: Ms. Jyoshita		
Time: 3: 00 Hours	Total Marks: 70	

Note: Attempt all Sections. If you require any missing data, then choose suitably.

SECTION A

1. Attempt *all* questions in brief.

Q No. Question Marks CO Define transconductance of JEFT. 2 2 a. Differentiate between avalanche and zener breakdown. 2 b. 1 What is RADAR ? Write down two applications of RADAR.. 2 1 C. 2 2 d. Find 1's and 2's complement of ; 10001100. List two advantages of modulation. 2 2 e. State two differences between FET and BJT. f. 2 1 Define CMRR. 2 2 g.

SECTION B

2. Attempt any *three* of the following:

7X3=21

2X7=14

Q No.	Question	Marks	CO
a.	Write down the characteristics of ideal op-pam . Derive the expression for gain	7	3
	of op-pam as non inverting amplifier.		
b.	Describe AM modulation and De- modulation technique with suitable diagram.	7	4
C.	Draw and explain common base N-P-N Transistor with its input and output	7	4
	characteristics graph. Also write the expression for output current.		
d.	State and Derive De – Morgan's law.	7	3
e.	What is the difference between clipper and clamper. Explain with the help of	7	4
	suitable diagram.		

SECTION C

3. Attempt any *one* part of the following:

7X1=7

Q No.	Question	Marks	CO
a.	With the help of neat circuit diagram, explain the working of a full wave bridge rectifier.	7	3
b.	Derive the relationship between current amplification factor for common emitter and common base configuration of a bipolar junction transistor.	7	4

4. Attempt any *one* part of the following:

Q No.	Question	Marks	CO
a.	Explain the working of enhancement type MOSFET along with their transfer	7	3
	characteristics.		
b.	Describe the construction and working of P- channel Depletion MOSFET with	7	4
	characteristics graph. Also justify that it is a voltage controlled device.		

5. Attempt any *one* part of the following:

Q No.	Question	Marks	CO
a.	What is an operational amplifier ? Draw its block diagram. Write the	7	5
	characteristics of an ideal op-pam.		
b.	What do you mean by IOT? Discuss its various components.	7	4

6. Attempt any *one* part of the following:

7X1= 7

Q No.	Question	Marks	CO
a.		7	4
	Simplify the following Boolean expression : $F(A,B,C,D,E) = \Sigma$ (2,4,6,8,5,7,9)		
	+d(6,11,13,16,18, 23 , 25 ,29)		
b.	Define universal logic gates. Why NAND and NOR gates are called as universal	7	5
	gates?		

7. Attempt any *one* part of the following:

7X1=7

Q No.	Question	Marks	CO
a.	Why do we need modulation? The antenna current of an AM transmitter is 8 A	7	4
	when only the carrier is sent, but it increases to 8.93 A , when the carrier is		
	modulated by a single sine wave. Find percentage modulation. Determine the		
	antenna current when the percentage modulation changes to 0.8.		
b.	What do you mean by satellite communication? Enlist its advantages	7	5

7X1=7